

Image AF/2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Andrew Marshall, et al.

Docket No: TI-31157

Serial No: 10/023,113

Conf. No: 2385

Examiner: Khiem D. Nguyen

Art Unit: 2823

Filed: 12/13/2001


For: MEMORY CELL WITH TRANSISTORS HAVING RELATIVELY HIGH THRESHOLD
VOLTAGES IN RESPONSE TO SELECTIVE GATE DOPING

AMENDMENT PURSUANT TO 37 CFR 1.116

Mail Stop AF
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8(a)

I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 12-2-03.


Ann Trent

Dear Sir:

Responsive to the Office Action mailed November 10, 2003, in connection with the above identified application, Applicants respectfully submit the following remarks.

Amendments to the Drawings:

None